
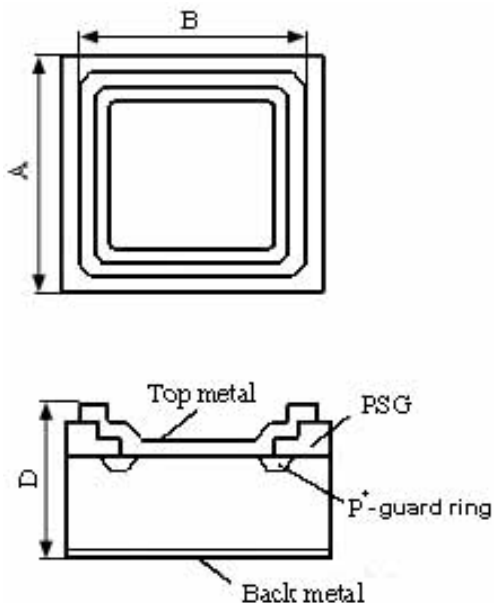


SCHOTTKY DIODES KDN-15040



Rev.1. Feb. 2010

|  VSP-MIKRON | | 15A/40V. Die Size-106mil. | | |
|--|-------------|----------------------------------|---------------------|-------------------------|
| Electrical Characteristics | Symbol | Unit | Spec. limit | Die Sort |
| Breakdown Voltage @ $I_R=10mA$ | V_{BR} | V | 40 | 45 |
| Average Rectified Forward Current | $I_{F(AV)}$ | A | 15,0 | - |
| DC Forward Voltage @ $25^{\circ}C, I_F=15,0A$ | V_F | V | 0,55 | 0,53 |
| Maximum Reverse Current @ $25^{\circ}C, V_R=45V$ @ $25^{\circ}C, V_R=40V$ @ $125^{\circ}C, V_R=40V$ | I_R | mA | - 0,300 160,0 | 0,300 0,200 150,0 |
| Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD) | I_{FSM} | A | 180 | - |
| Peak Repetitive Reverse Surge Current @ $2,0\mu s, f=1kHz., T_J < 150^{\circ}C.$ | I_{RRM} | A | 4,0 | |
| Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact. | ESD | kV | ± 8 (contact) | |
| Voltage Rate of Change | dV/dt | V/ μS | 10.000 | |
| Operating Junction Temperature | T_J | $^{\circ}C$ | 150 | |



| DIM | ITEM | μm |
|-------------------|---------------------|---------|
| A_x A_y | Wafer Form Die Size | 2700 |
| B_x B_y | Top Metal Size | 2560 |
| D | Thickness | 350max. |
| Scribe line Width | | 80 |

Top metal: a) **Al** – for Wire Bonding;
 b) **Al-Ni-Ag** – for Soldering.
 Backside metal: **Ti-Ni-Ag**.